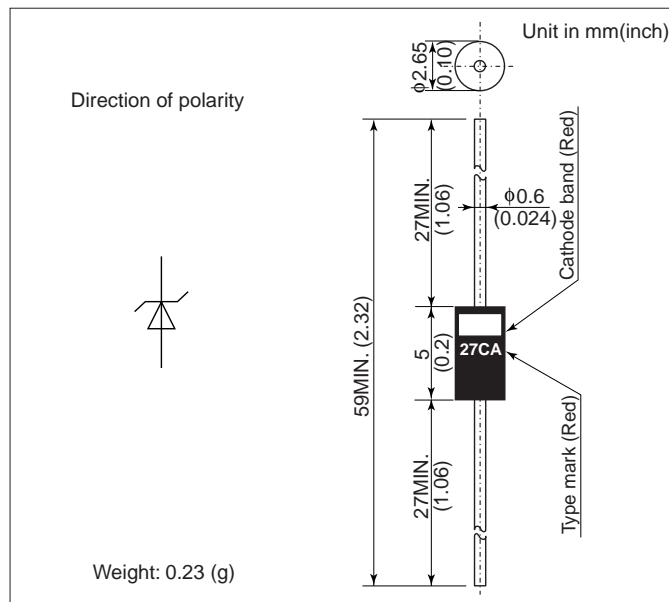


# DAM1A

## FEATURES

- High transient reverse power capability suitable for protecting automobile electronic components etc.
- Diffused-junction. Resin encapsulated.

## OUTLINE DRAWING



## ABSOLUTE MAXIMUM RATINGS

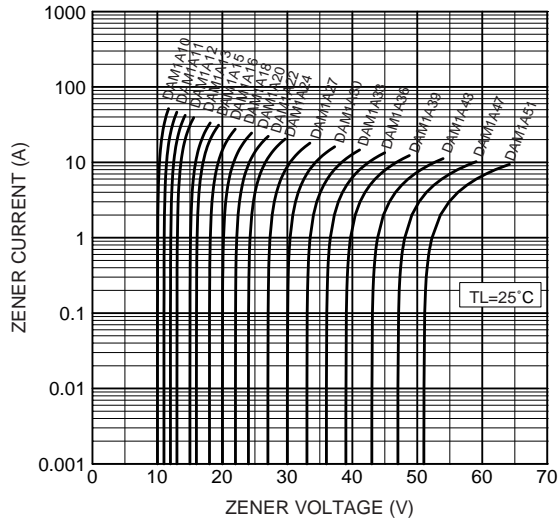
Items	Symbols	Units	Ratings
Non-Repetitive Peak Reverse One-Cycle Dissipation	$P_{RSM}$	W	600(Rectangular pulse $t=0.1ms$ $T_i=25^{\circ}C$ start)
Operating Junction Temperature	$T_j$	$^{\circ}C$	-40 ~ +150
Storage Temperature	$T_{stg}$	$^{\circ}C$	-40 ~ +150
DC Reverse Voltage	$V_{DC}$	V	Refer to characteristics column

## CHARACTERISTICS( $T_L=25^{\circ}C$ )

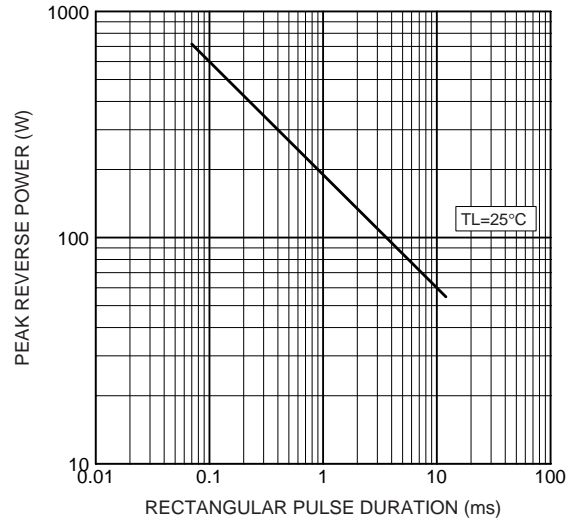
Type	DC Reverse Voltage $V_{DC}$ (V)	Characteristics				Maximum Reverse Current	
		Zener Voltage $V_z$ (V)		Maximum Dynamic Impedance $Z_z$ (ohm)	Test Current $I_z$ (mA)	$I_{RRM}$ ( $\mu A$ )	$V_R$ (V)
		Minimum	Maximum				
DAM1A10	7	9.4	10.6	15	25	50	7
DAM1A11	8	10.4	11.6	15	25	50	8
DAM1A12	9	11.4	12.7	15	25	50	9
DAM1A13	10	12.4	14.1	15	25	50	10
DAM1A15	11	13.5	15.6	15	25	50	11
DAM1A16	12	15.3	17.1	15	15	50	12
DAM1A18	13	16.8	19.1	15	15	50	13
DAM1A20	14	18.8	21.2	15	15	50	14
DAM1A22	16	20.8	23.3	15	15	50	16
DAM1A24	18	22.7	25.6	15	10	50	18
DAM1A27	20	25.1	28.9	15	10	50	20
DAM1A30	22	28.0	32.0	15	10	50	22
DAM1A33	24	31.0	35.0	15	10	50	24
DAM1A36	26	33.4	38.6	15	10	50	26
DAM1A39	28	36.1	41.9	30	10	50	28
DAM1A43	31	39.8	46.2	30	6	50	31
DAM1A47	34	43.3	50.7	30	6	50	34
DAM1A51	37	46.9	55.1	30	6	50	37

# DAM1A

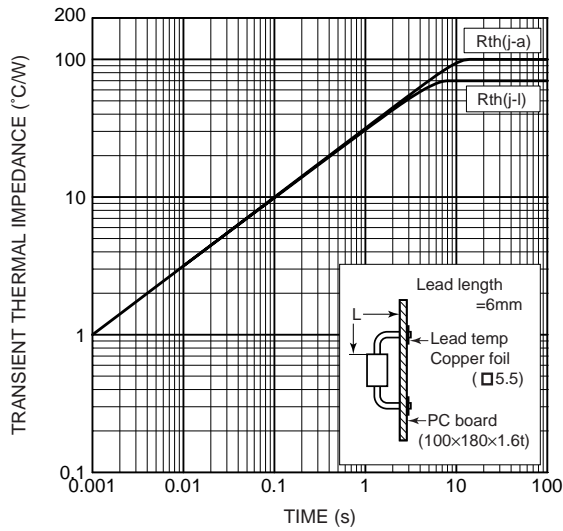
Typical zener characteristics



Typical reverse power characteristic (Rectangular pulse non-repetitive)



Transient thermal impedance



# HITACHI POWER SEMICONDUCTORS

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